

# isc Silicon NPN Power Transistors

### **DESCRIPTION**

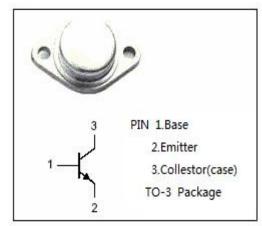
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 140V(Min)
- · High Power Dissipation-
  - : P<sub>C</sub>= 100W(Max)@T<sub>C</sub>=25℃
- · Complement to Type 2SB555
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

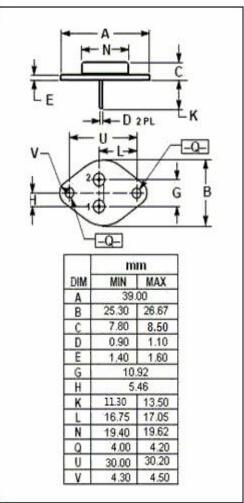


- · Designed for power amplifier applications.
- Recommended for high-fidelity audio frequency amplifier output stage.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER  | VALUE   | UNIT       |
|------------------|--|---------|------------|
| V <sub>СВО</sub> | Collector-Base Voltage                               | 140     | V          |
| $V_{\text{CEO}}$ | Collector-Emitter Voltage                            | 140     | ٧          |
| V <sub>EBO</sub> | Emitter-Base Voltage                                 | 5       | V          |
| Ic               | Collector Current-Continuous                         | 12      | Α          |
| IE               | Emitter Current-Continuous                           | 12      | Α          |
| Pc               | Collector Power Dissipation<br>@T <sub>C</sub> =25°C | 100     | W          |
| TJ               | Junction Temperature                                 | 150     | $^{\circ}$ |
| T <sub>stg</sub> | Storage Temperature                                  | -65~150 | $^{\circ}$ |







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2SD425

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS   | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| $V_{(BR)CEO}$        | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 10mA; I <sub>B</sub> = 0          | 140 |      |     | ٧    |
| V <sub>(BR)EBO</sub> | Emitter-Base Breakdown Voltage       | I <sub>E</sub> = 1mA; I <sub>C</sub> = 0           | 5   |      |     | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 7A; I <sub>B</sub> = 0.7A         |     |      | 3.0 | V    |
| V <sub>BE(on)</sub>  | Base-Emitter On Voltage              | I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V          |     |      | 2.5 | ٧    |
| Ісво                 | Collector Cutoff Current             | V <sub>CB</sub> = 60V; I <sub>E</sub> = 0          |     |      | 0.1 | mA   |
| I <sub>EBO</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = 5V; I <sub>C</sub> = 0           |     |      | 0.1 | mA   |
| h <sub>FE</sub>      | DC Current Gain                      | I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V          | 40  |      | 140 |      |
| Сов                  | Output Capacitance                   | I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz |     | 330  |     | pF   |
| f⊤                   | Current-Gain—Bandwidth Product       | I <sub>E</sub> = 2A; V <sub>CE</sub> = 5V          |     | 6    |     | MHz  |

### h<sub>FE</sub> Classifications

| R     | 0      |
|-------|--------|
| 40-80 | 70-140 |

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